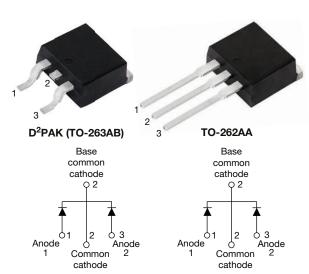
## VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

Vishay Semiconductors

# Ultrafast Rectifier, 2 x 10 A FRED Pt®



VS-MURB2020CT-M3

VS-MURB2020CT-1-M3

#### **LINKS TO ADDITIONAL RESOURCES**



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	2 x 10 A					
V <sub>R</sub>	200 V					
V <sub>F</sub> at I <sub>F</sub>	0.85 V					
t <sub>rr</sub>	35 ns					
T <sub>J</sub> max.	175 °C					
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA					
Circuit configuration	Common cathode					

#### **FEATURES**

- · Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

### **MECHANICAL DATA**

Case: D<sup>2</sup>PAK (TO-263AB), TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V			
Average rectified forward current	per leg	1		10				
Average rectilied forward current	total device	I <sub>F(AV)</sub>	Rated V <sub>R</sub> , T <sub>C</sub> = 145 °C	20				
Non-repetitive peak surge current p	er leg	I <sub>FSM</sub>		100	A			
Peak repetitive forward current per leg		I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 145 °C	20				
Operating junction and storage tem	peratures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C			

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	I <sub>R</sub> = 100 μA	200	-	-			
		I <sub>F</sub> = 8 A, T <sub>J</sub> = 125 °C	ı	-	0.85	V		
Forward voltage	$V_{F}$	I <sub>F</sub> = 16 A	ı	-	1.15	v		
		I <sub>F</sub> = 16 A, T <sub>J</sub> = 125 °C	ı	-	1.05			
Reverse leakage current	1	$V_R = V_R$ rated	-	-	15			
neverse leakage current	I <sub>R</sub>	$T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	ı	-	250	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	55	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body		8.0	-	nH		

Reverse recovery charge

# VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

# Vishay Semiconductors

78

nC

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST COI	TEST CONDITIONS			MAX.	UNITS	
		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	A/μs, V <sub>R</sub> = 30 V	-	-	35		
D		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	19	-	1	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	21	-	ns - A	
		T <sub>J</sub> = 125 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 160 \text{ V}$	-	35	-		
Dools we see your assument		T <sub>J</sub> = 25 °C		-	1.9	-		
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	4.8	-		
Davidas vasavias akasas	0	T <sub>J</sub> = 25 °C	] VH = 100 V	-	25	-	0	

 $Q_{rr}$ 

T<sub>J</sub> = 125 °C

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance, junction-to-case per leg	R <sub>thJC</sub>		-	-	2.5			
Thermal resistance, junction-to-ambient per leg	R <sub>thJA</sub>		-	-	50	°C/W		
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking davice		Case style D <sup>2</sup> PAK (TO-263AB) MI			URB2020CT			
Marking device		Case style TO-262AA		MURB2	020CT-1			

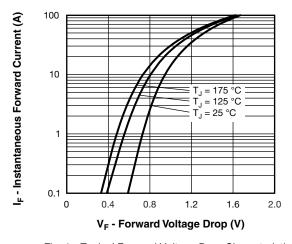


Fig. 1 - Typical Forward Voltage Drop Characteristics

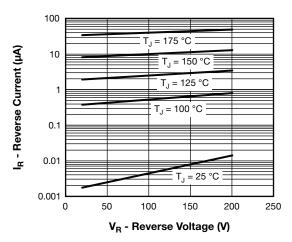


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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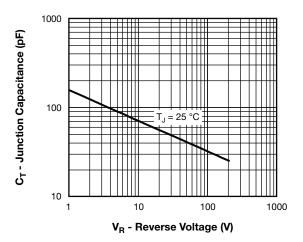


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

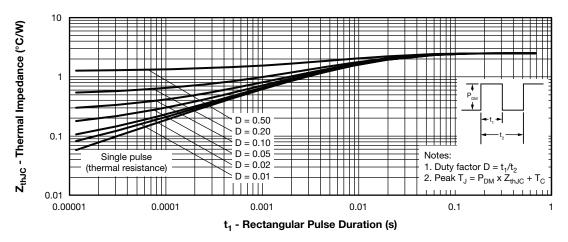


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

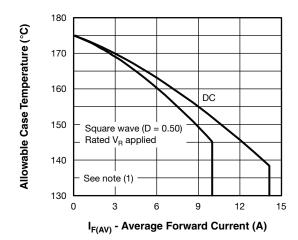


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

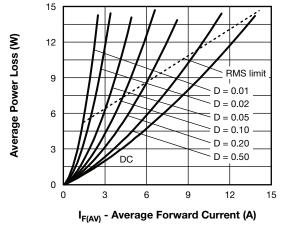


Fig. 6 - Forward Power Loss Characteristics

### Note

<sup>&</sup>lt;sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;  $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$  (see fig. 6);  $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1} = rated V_R$ 

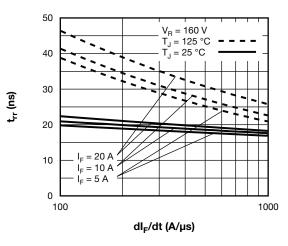


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

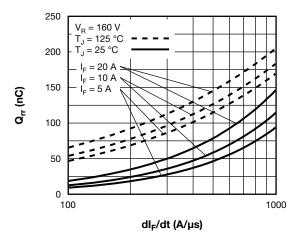
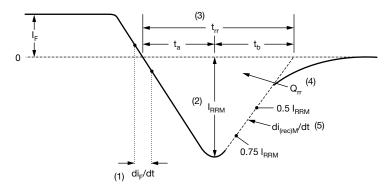


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_r$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

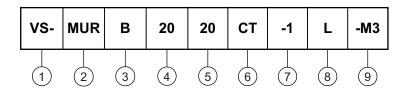
Fig. 9 - Reverse Recovery Waveform and Definitions

# **VS-MURB2020CT-M3, VS-MURB2020CT-1-M3**

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### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

3 - B =  $D^2$ PAK (TO-263AB) / TO-262AA

- Current rating (20 = 20 A)

5 - Voltage rating (20 = 200 V)

6 - CT = center tap (dual) TO-220 / D<sup>2</sup>PAK (TO-263AB) / TO-262AA

7 - • -1 = TO-262AA

• None = D<sup>2</sup>PAK (TO-263AB)

None = tube (50 pieces)

• L = tape and reel (left oriented, for D<sup>2</sup>PAK (TO-263AB) package)

• R = tape and reel (right oriented, for D<sup>2</sup>PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-MURB2020CTL-M3	800	13" diameter plastic tape and reel				
VS-MURB2020CT-M3	50	Antistatic plastic tubes				
VS-MURB2020CTR-M3	800	13" diameter plastic tape and reel				
VS-MURB2020CT-1-M3	50	Antistatic plastic tubes				

LINKS TO RELATED DOCUMENTS		
Dimensions —	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
— Differsions	TO-262AA	www.vishay.com/doc?96165
Part marking information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444
Part marking information —	TO-262AA	www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424
SPICE model		www.vishay.com/doc?96995



# Vishay Semiconductors

## D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	EC CYMPOL	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

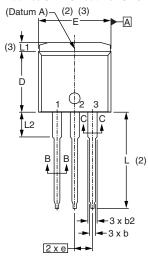


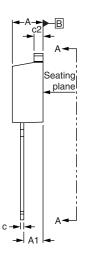
## Vishay Semiconductors

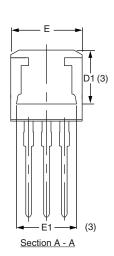
### **TO-262AA**

### **DIMENSIONS** in millimeters and inches

#### Modified JEDEC® outline TO-262







**⊕** 0.010 **M** A**M** B

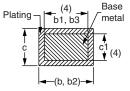
#### Lead assignments



**Diodes** 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	IETERS	INC	INCHES			
	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.10	0 BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

#### **Notes**

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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